

Product features

High precision machining technology

Low temperature drift, high power.

Ceramic substrate, 50 Ω coplanar waveguide

Gold wire bonding

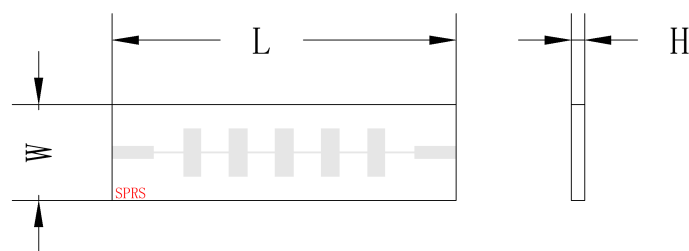
Tech specifications

Items	Parameters	Units
Center Frequency	18.4	GHz
Bandwidth	DC-36.8	GHz
Passband IL	2.0	dB
Ripple	2.0	dB
VSWR	1.7:1	
Group delay ripple	0.4	ns
Rejection	25@41.2-48.0GHz	dBc

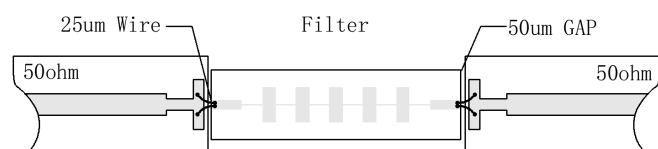
Other requirement (Design assurance)

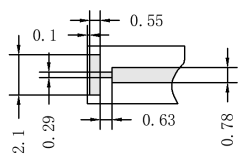
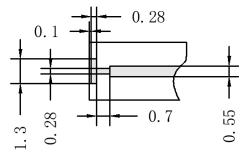
power	1W CW
Work Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L:3.5, W:2.0, h:0.26

Outline drawing: Port centered

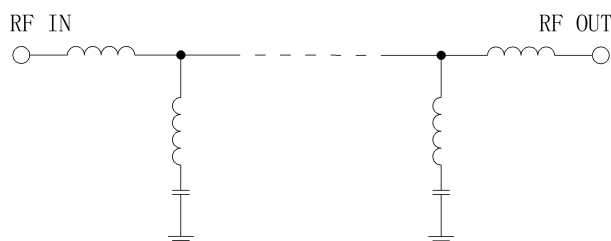


Suggested PCB Layout

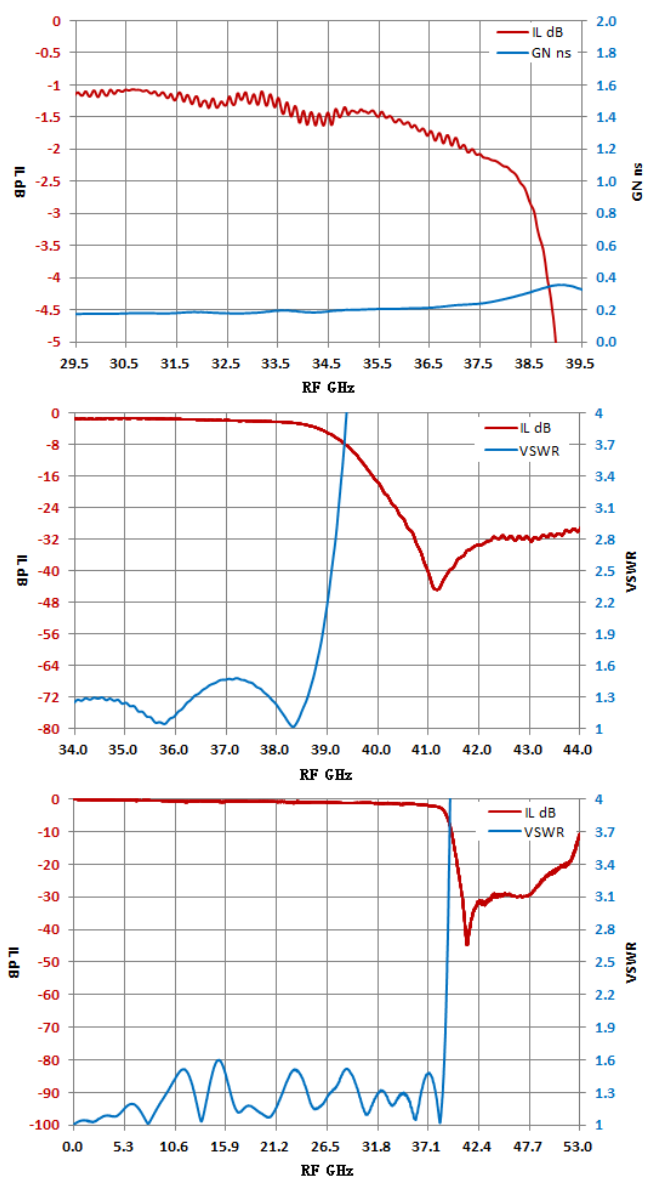


PCB Rogers5880, h: 0.254mm	PCB Rogers4350B, h: 0.254mm
	

Schematic diagram



Typical test curve



Note: The specifications and performance data contained in this data sheet are based on tests established by CMW.

Note

1: 0.1mm from the side wall, 1.75mm from the surface to the upper cover.

2: Suggest using conductive adhesive for bonding;

3: The chip should be installed on kovar alloy or molybdenum copper;

4: Suggest using a T-shaped structure for microstrip bonding.